MOSFET – Dual, N-Channel, Small Signal, SC-88

30 V, 250 mA

Features

- Low Gate Charge for Fast Switching
- Small Footprint 30% Smaller than TSOP–6
- ESD Protected Gate
- AEC Q101 Qualified NVTJD4001N
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Low Side Load Switch
- Li-Ion Battery Supplied Devices Cell Phones, PDAs, DSC
- Buck Converters
- Level Shifts

MAXIMUM RATINGS (T_J = 25° C unless otherwise stated)

Param	Symbol	Value	Units		
Drain-to-Source Voltage	V _{DSS}	30	V		
Gate-to-Source Voltage	l		V _{GS}	±20	V
Continuous Drain	$\begin{array}{c} \mbox{ prinuous Drain} \\ \mbox{ urrent (Note 1)} \end{array} & \begin{array}{c} \mbox{ Steady} \\ \mbox{ State} \end{array} & \begin{array}{c} \mbox{ T}_{A} = 25 \\ \mbox{ T}_{A} = 85 \end{array} \end{array}$		I _D	250	mA
				180	
Power Dissipation (Note 1)			PD	272	mW
Pulsed Drain Current	I _{DM}	600	mA		
Operating Junction and S	T _J , T _{STG}	–55 to 150	°C		
Source Current (Body Di	۱ _S	250	mA		
Lead Temperature for So (1/8" from case for 10 s)	ΤL	260	°C		

THERMAL RESISTANCE RATINGS (Note 1)

Parameter	Symbol	Value	Unit
Junction-to-Ambient - Steady State	$R_{\theta JA}$	458	°C/W
Junction-to-Lead - Steady State	$R_{\theta JL}$	252	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

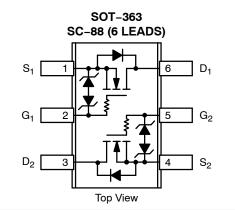
1. Surface mounted on FR4 board using min pad size (Cu area = 0.155 in sq [1 oz] including traces).

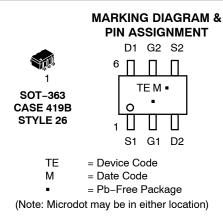


ON Semiconductor®

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V _{(BR)DSS}	V _{(BR)DSS} R _{DS(on)} TYP		
30 V	1.0 Ω @ 4.0 V	250 mA	
	1.5 Ω @ 2.5 V	230 MA	





ORDERING INFORMATION

Device	Package	Shipping [†]
NTJD4001NT1G	SOT-363 (Pb-Free)	3000 / Tape & Reel
NVTJD4001NT1G	SOT-363 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

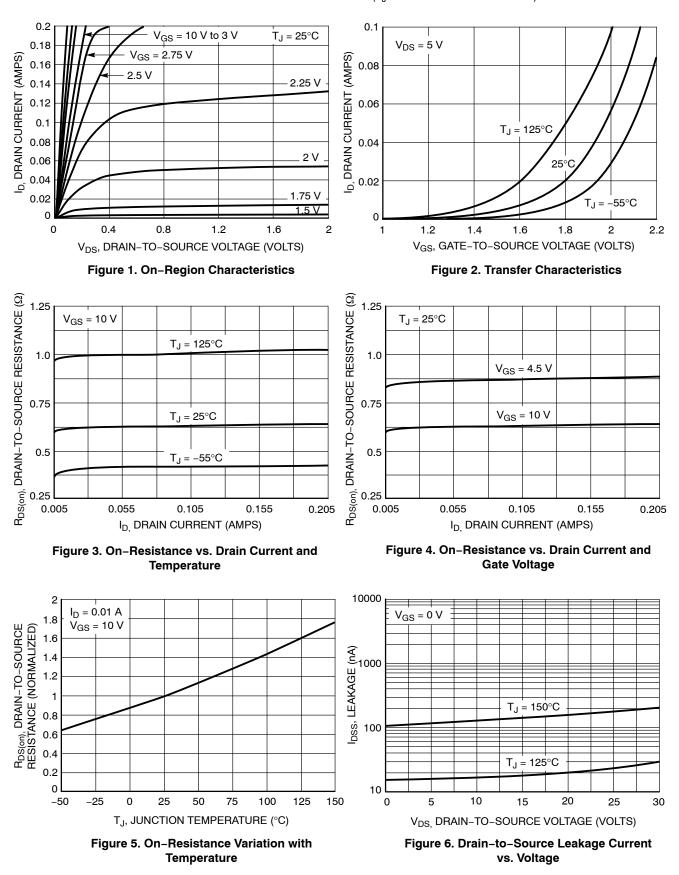
Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
OFF CHARACTERISTICS	·					
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V_{GS} = 0 V, I_D = 100 μ A	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			56		mV/ °C
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V, V_{DS} = 30 V$			1.0	μΑ
Gate-to-Source Leakage Current	I _{GSS}	V_{DS} = 0 V, V_{GS} = ±10 V			±1.0	μΑ
ON CHARACTERISTICS (Note 2)	· · ·					
Gate Threshold Voltage	V _{GS(TH)}	V_{GS} = V_{DS} , I_D = 100 μ A	0.8	1.2	1.5	V
Gate Threshold Temperature Coefficient	V _{GS(TH)} /T _J			-3.2		mV/ °C
Drain-to-Source On Resistance	R _{DS(on)}	V_{GS} = 4.0 V, I _D = 10 mA		1.0	1.5	Ω
		V_{GS} = 2.5 V, I _D = 10 mA		1.5	2.5	
Forward Transconductance	9FS	V_{DS} = 3.0 V, I _D = 10 mA		80		mS
CHARGES AND CAPACITANCES	· · · · ·					
Input Capacitance	C _{ISS}	$V_{GS} = 0 V, f = 1.0 MHz,$		20	33	pF
Output Capacitance	C _{OSS}	V _{DS} = 5.0 V		19	32	
Reverse Transfer Capacitance	C _{RSS}			7.25	12	
Total Gate Charge	Q _{G(TOT)}	$V_{GS} = 5.0 \text{ V}, V_{DS} = 24 \text{ V},$		0.9	1.3	nC
Threshold Gate Charge	Q _{G(TH)}	$I_D = 0.1 \text{ \AA}$		0.2		
Gate-to-Source Charge	Q _{GS}			0.3		
Gate-to-Drain Charge	Q _{GD}			0.2		
SWITCHING CHARACTERISTICS (No	ote 3)					
Turn-On Delay Time	td _(ON)	$V_{GS} = 4.5 \text{ V}, V_{DD} = 5.0 \text{ V},$		17		ns
Rise Time	tr	I_D = 10 mA, R_G = 50 Ω		23		
Turn-Off Delay Time	td _(OFF)			94		7
Fall Time	tf			82		
DRAIN-SOURCE DIODE CHARACTE	RISTICS					÷
	N/			0.65	0.7	

Forward Diode Voltage	V _{SD}	$V_{GS} = 0 V$,	$T_J = 25^{\circ}C$	0.65	0.7	V
		l _S = 10 mA	T _J = 125°C	0.45		
Reverse Recovery Time	t _{RR}	$\label{eq:VGS} \begin{array}{l} V_{GS} = 0 \ V, \ dI_S/dt = 8.0 \ A/\mu s, \\ I_S = 10 \ mA \end{array}$		12.4		ns

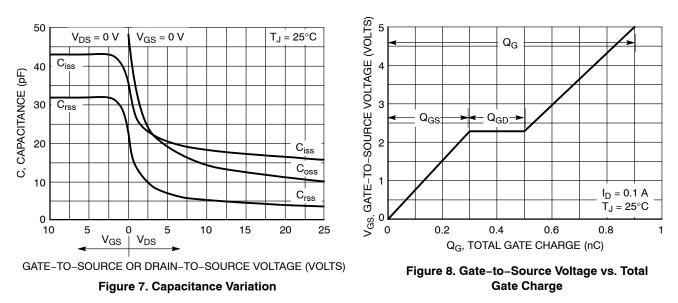
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: pulse width \leq 300 μ s, duty cycle \leq 2%.

3. Switching characteristics are independent of operating junction temperatures.



TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)



TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

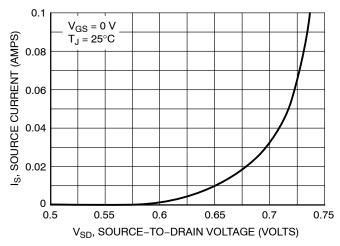
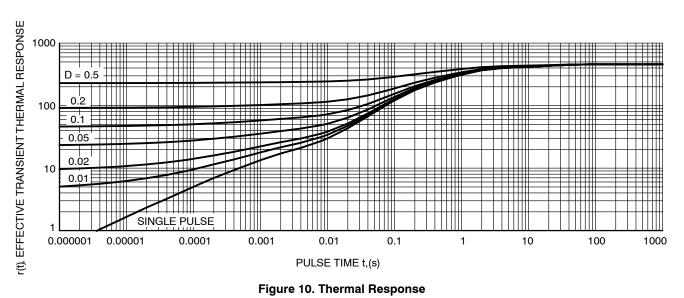


Figure 9. Diode Forward Voltage vs. Current



0.043

0.004





- XXX = Specific Device Code

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering

details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DATE 11 DEC 2012

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13:	STYLE 14:	STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:
PIN 1. ANODE	PIN 1. VREF	PIN 1. ANODE 1	PIN 1. BASE 1	PIN 1. BASE 1	PIN 1. VIN1
2. N/C	2. GND	2. ANODE 2	2. EMITTER 2	2. EMITTER 1	2. VCC
3. COLLECTOR	3. GND	3. ANODE 3	3. COLLECTOR 2	3. COLLECTOR 2	3. VOUT2
4. EMITTER	4. IOUT	4. CATHODE 3	4. BASE 2	4. BASE 2	4. VIN2
5. BASE	5. VEN	5. CATHODE 2	5. EMITTER 1	5. EMITTER 2	5. GND
6. CATHODE	6. VCC	6. CATHODE 1	6. COLLECTOR 1	6. COLLECTOR 1	6. VOUT1
STYLE 19:	STYLE 20:	STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:
PIN 1. I OUT	PIN 1. COLLECTOR	PIN 1. ANODE 1	PIN 1. D1 (i)	PIN 1. Vn	PIN 1. CATHODE
2. GND	2. COLLECTOR	2. N/C	2. GND	2. CH1	2. ANODE
3. GND	3. BASE	3. ANODE 2	3. D2 (i)	3. Vp	3. CATHODE
4. V CC	4. EMITTER	4. CATHODE 2	4. D2 (c)	4. N/C	4. CATHODE
5. V EN	5. COLLECTOR	5. N/C	5. VBUS	5. CH2	5. CATHODE
6. V REF	6. COLLECTOR	6. CATHODE 1	6. D1 (c)	6. N/C	6. CATHODE
STYLE 25:	STYLE 26:	STYLE 27:	STYLE 28:	STYLE 29:	STYLE 30:
PIN 1. BASE 1	PIN 1. SOURCE 1	PIN 1. BASE 2	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. SOURCE 1
2. CATHODE	2. GATE 1	2. BASE 1	2. DRAIN	2. ANODE	2. DRAIN 2
3. COLLECTOR 2	3. DRAIN 2	3. COLLECTOR 1	3. GATE	3. COLLECTOR	3. DRAIN 2
4. BASE 2	4. SOURCE 2	4. EMITTER 1	4. SOURCE	4. EMITTER	4. SOURCE 2
5. EMITTER	5. GATE 2	5. EMITTER 2	5. DRAIN	5. BASE/ANODE	5. GATE 1
6. COLLECTOR 1	6. DRAIN 1	6. COLLECTOR 2	6. DRAIN	6. CATHODE	6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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